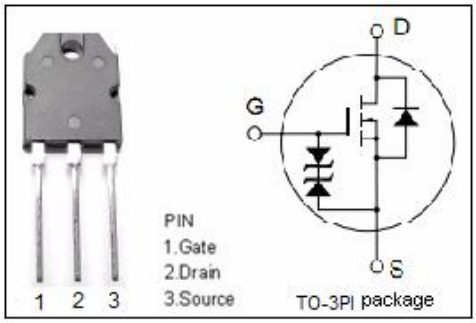
isc N-Channel MOSFET Transistor 2SK2150

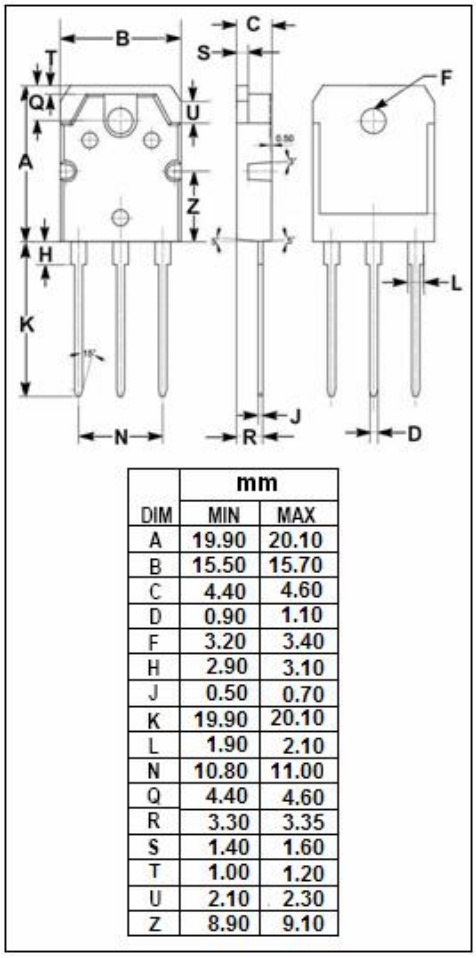
DESCRIPTION

- Drain Current I_D= 15A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}= 500V(Min)
- Fast Switching Speed



APPLICATIONS

- Switching regulators
- General purpose power amplifier



DIM	mm MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.40	4.60
D	0.90	1.10
F	3.20	3.40
H	2.90	3.10
J	0.50	0.70
K	19.90	20.10
L	1.90	2.10
N	10.80	11.00
Q	4.40	4.60
R	3.30	3.35
S	1.40	1.60
T	1.00	1.20
U	2.10	2.30
Z	8.90	9.10

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	500	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Drain Current-continuous@ TC=25℃	15	A
$I_{D(puls)}$	Pulsed Drain Current	60	A
P_{tot}	Total Dissipation@T_C=25℃	150	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	0.833	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance, Junction to Ambient	50	℃/W

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• **ELECTRICAL CHARACTERISTICS (T_C=25℃)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= 10mA	500			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=10V; I_D=1mA	2.0		4.0	V
V_{DS}	Diode Forward Voltage	I_{DR}=15A ;V_{GS}= 0			1.7	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D= 7A		0.29	0.4	Ω
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±25V;V_{DS}= 0			±10	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 500V; V_{GS}= 0			100	μA
Ciss	Input Capacitance	V_{DS}=25V; V_{GS}=0V; f_T=1MHz		2350		pF
Crss	Reverse Transfer Capacitance			200		
Coss	Output Capacitance			730		
t_r	Rise Time	V_{GS}=10V; I_D=7A; V_{DD}=210V; R_L=30Ω		20		ns
t_{on}	Turn-on Time			55		
t_f	Fall Time			40		
t_{off}	Turn-off Time			235		

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